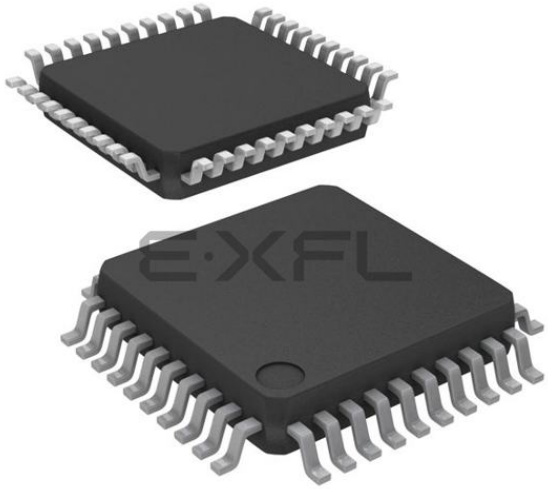
Renesas Electronics America Inc - R5F10RBAAFP#X0 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	20
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 4x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10rbaafp-x0

Pin count	Package	Fields of Application [Note]	Part Number
32 pins	32-pin plastic LQFP (7 × 7)	A	R5F10RB8AFP, R5F10RBAAFP, R5F10RBCAFP
		G	R5F10RB8GFP, R5F10RBAGFP, R5F10RBCGFP
44 pins	44-pin plastic LQFP (10 × 10)	A	R5F10RF8AFP, R5F10RFAAFP, R5F10RFCAFP
		G	R5F10RF8GFP, R5F10RFAGFP, R5F10RFCGFP
48 pins	48-pin plastic LQFP (fine pitch) (7 × 7)	A	R5F10RG8AFB, R5F10RGAAFB, R5F10RGCAFB
		G	R5F10RG8GFB, R5F10RGAGFB, R5F10RGCGFB
52 pins	52-pin plastic LQFP (10 × 10)	A	R5F10RJ8AFA, R5F10RJAAFA, R5F10RJCAFA
		G	R5F10RJ8GFA, R5F10RJAGFA, R5F10RJCGFA
64 pins	64-pin plastic WQFN (8 × 8)	A	R5F10RLAANB, R5F10RLCANB
		G	R5F10RLAGNB, R5F10RLCGNB
	64-pin plastic LQFP (fine pitch) (10 × 10)	A	R5F10RLAAFB, R5F10RLCAFB
		G	R5F10RLAGFB, R5F10RLCGFB
	64-pin plastic LQFP (12 × 12)	A	R5F10RLAAFA, R5F10RLCAFA
		G	R5F10RLAGFA, R5F10RLCGFA

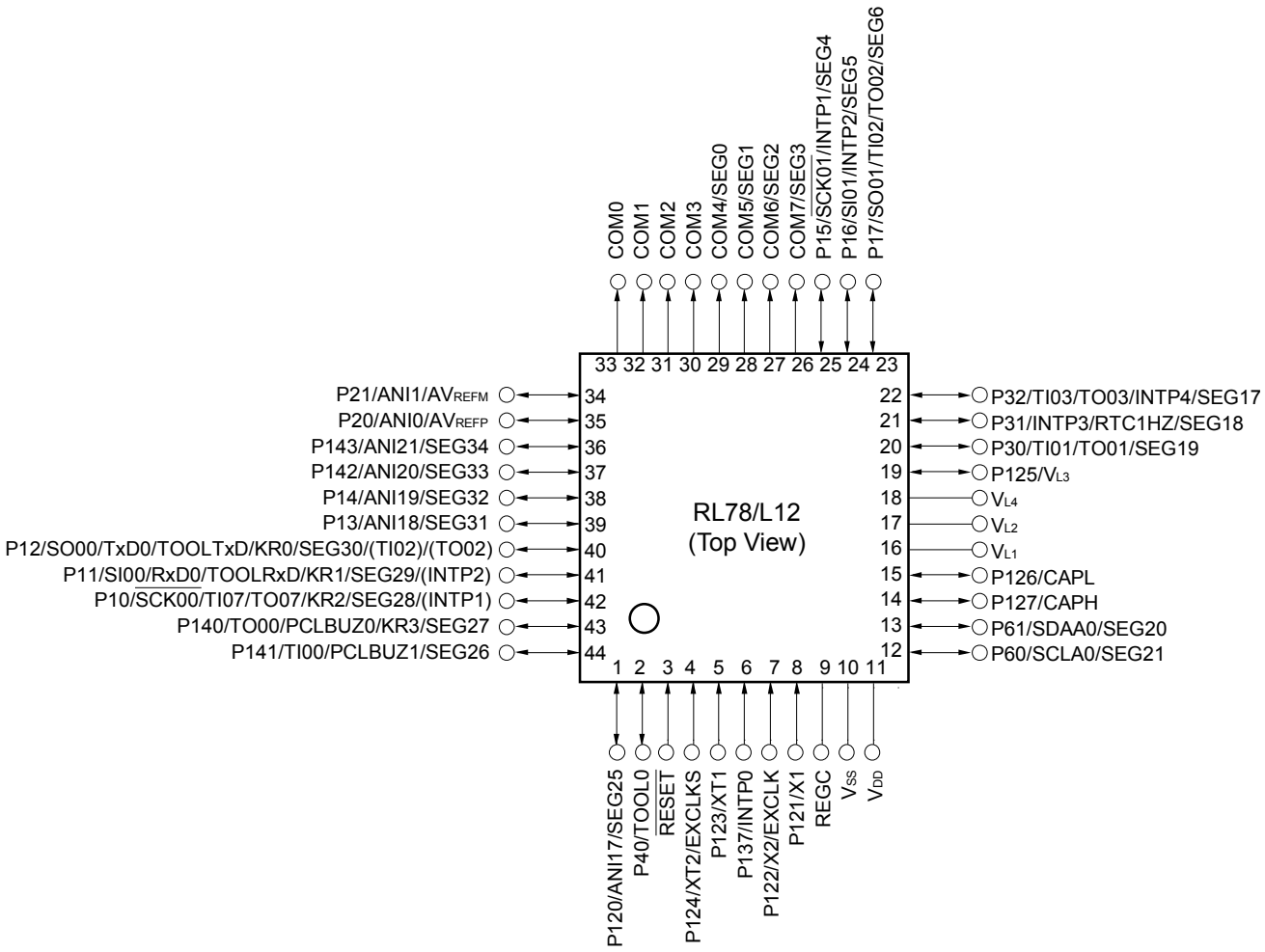
Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/L12**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.2 44-pin products

- 44-pin plastic LQFP (10 × 10)

<R>



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (3/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV_{DD}		EV_{DD}	V
	V_{IH2}	P10, P11, P15, P16	TTL input buffer 4.0 V ≤ EV_{DD} ≤ 5.5 V	2.2		EV_{DD}	V
			TTL input buffer 3.3 V ≤ EV_{DD} < 4.0 V	2.0		EV_{DD}	V
			TTL input buffer 1.6 V ≤ EV_{DD} < 3.3 V	1.50		EV_{DD}	V
	V_{IH3}	P20, P21		0.7V_{DD}		V_{DD}	V
	V_{IH4}	P60, P61		0.7EV_{DD}		EV_{DD}	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0.8V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2EV_{DD}	V
	V_{IL2}	P10, P11, P15, P16	TTL input buffer 4.0 V ≤ EV_{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ EV_{DD} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EV_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P20, P21		0		0.3V_{DD}	V
	V_{IL4}	P60, P61		0		0.3EV_{DD}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		0.2V_{DD}	V

Caution The maximum value of V_{IH} of P10, P12, P15, P17 is EV_{DD}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.4 AC Characteristics

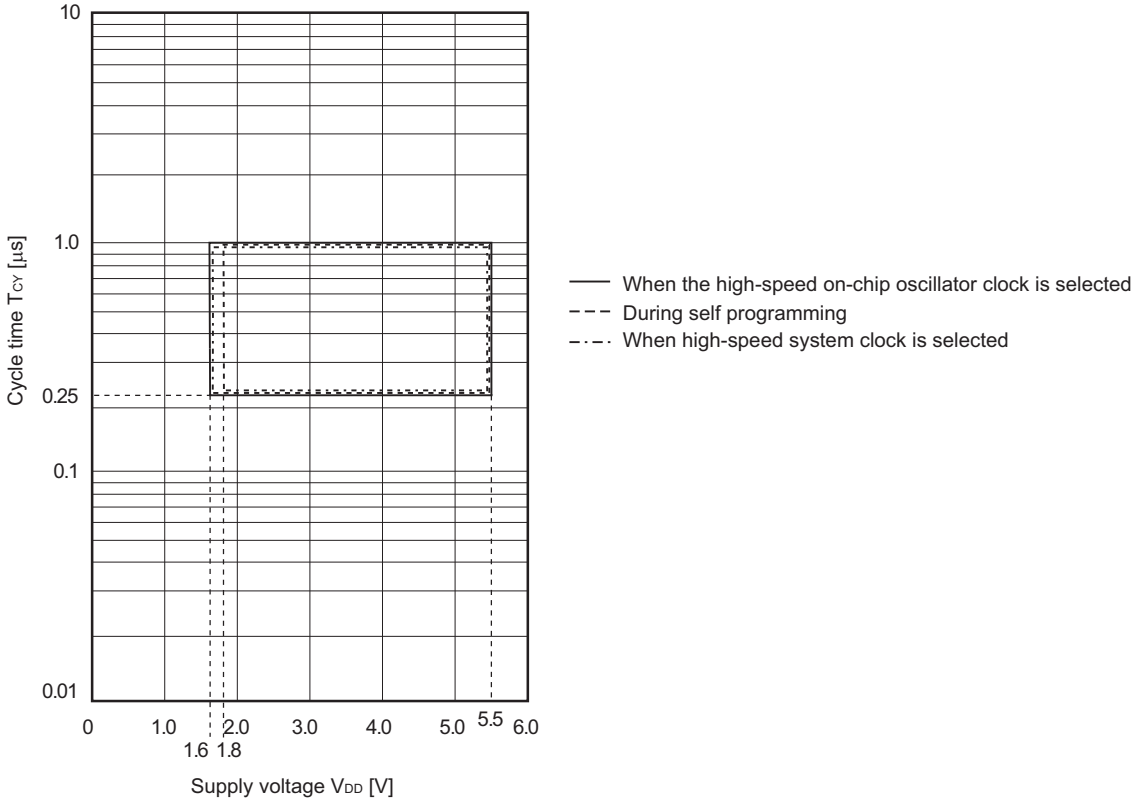
2.4.1 Basic operation

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

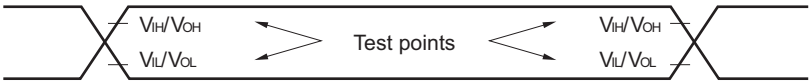
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LV (low voltage main) mode	1.6 V ≤ V_{DD} ≤ 5.5 V	0.25		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
		Subsystem clock (f_{SUB}) operation		1.8 V ≤ V_{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LV (low voltage main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.25		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
		1.8 V ≤ V_{DD} < 2.4 V			1.0		8.0	MHz
		1.6 V ≤ V_{DD} < 1.8 V			1.0		4.0	MHz
	f_{EXS}				32		35	kHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
		1.8 V ≤ V_{DD} < 2.4 V			60			ns
		1.6 V ≤ V_{DD} < 1.8 V			120			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK}+10			ns
TO00 to TO07 output frequency	f_{TO}	HS (high-speed main) mode		4.0 V ≤ EV_{DD} ≤ 5.5 V			16	MHz
				2.7 V ≤ EV_{DD} < 4.0 V			8	MHz
				2.4 V ≤ EV_{DD} < 2.7 V			4	MHz
		LS (low-speed main) mode		1.8 V ≤ EV_{DD} ≤ 5.5 V			4	MHz
		LV (low voltage main) mode		1.6 V ≤ EV_{DD} ≤ 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode		4.0 V ≤ EV_{DD} ≤ 5.5 V			16	MHz
				2.7 V ≤ EV_{DD} < 4.0 V			8	MHz
				2.4 V ≤ EV_{DD} < 2.7 V			4	MHz
		LS (low-speed main) mode		1.8 V ≤ EV_{DD} ≤ 5.5 V			4	MHz
		LV (low-voltage main) mode		1.8 V ≤ EV_{DD} ≤ 5.5 V			4	MHz
				1.6 V ≤ EV_{DD} < 1.8 V			2	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0		1.6 V ≤ V_{DD} ≤ 5.5 V	1			μs
		INTP1 to INTP7		1.6 V ≤ EV_{DD} ≤ 5.5 V	1			μs
Key interrupt input low-level width	t_{KR}	KR0 to KR3		1.8 V ≤ EV_{DD} ≤ 5.5 V	250			ns
				1.6 V ≤ EV_{DD} < 1.8 V	1			μs
$\overline{RESET}$ low-level width	t_{RSL}				10			μs

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

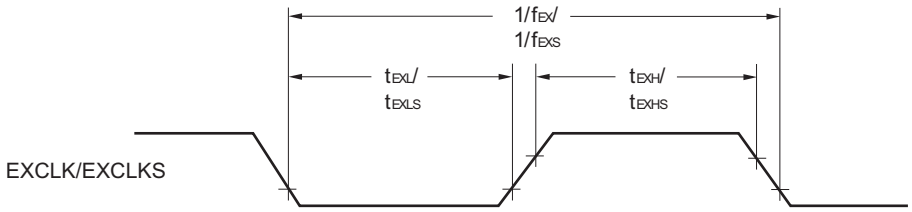
T_{CY} vs V_{DD} (LV (low-voltage main) mode)



AC Timing Test Points

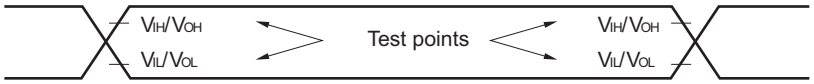


External System Clock Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		4.0		1.3		0.6	Mbps
		1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V				f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2				1.3		0.6	Mbps
		1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V						f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2						0.6	Mbps

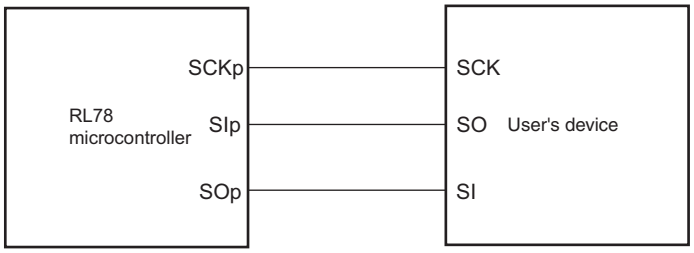
Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

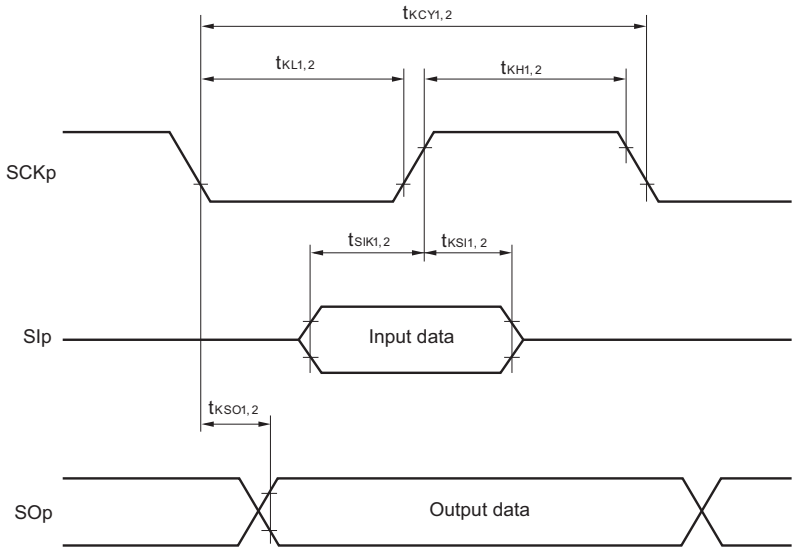
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

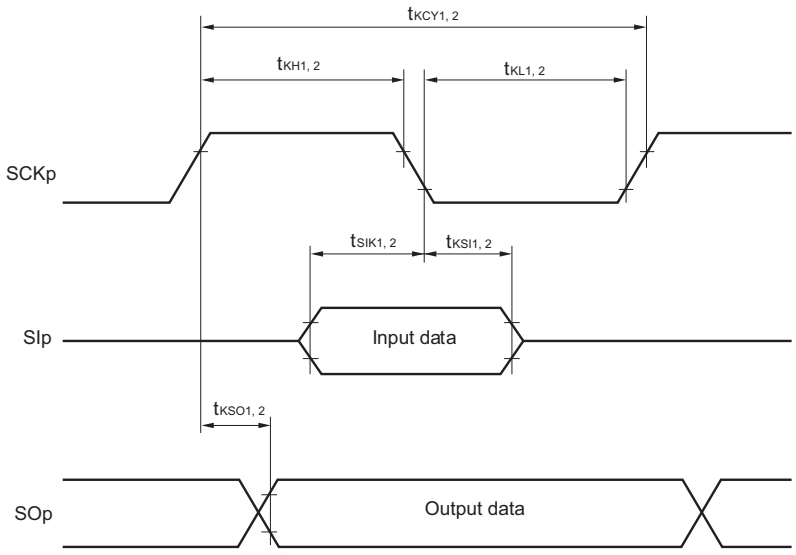
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01)

2. m: Unit number, n: Channel number (mn = 00, 01)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	19		19		19		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ			19		19		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		25		25		25	ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25		25	ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		25		25		25	ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ				25		25	ns

Notes
1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
3. Use it with $EV_{DD} \geq V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (32-pin to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0, ANI1	–	Refer to **2.6.1 (3)**.	Refer to **2.6.1 (4)**.
ANI16 to ANI23	Refer to **2.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **2.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, 1.6 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ V_{DD} ≤ 5.5 V		1.2	±3.5	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V [Note 4]		1.2	±7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 4]			±0.50	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
			1.6 V ≤ AV_{REFP} ≤ 5.5 V [Note 4]			±0.50	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ V_{DD} ≤ 5.5 V			±2.5	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V [Note 4]			±5.0	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ V_{DD} ≤ 5.5 V			±1.5	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V [Note 4]			±2.0	LSB
Analog input voltage	V_{AIN}	Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} [Note 5]			V
	V_{BGR}	Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} [Note 5]			V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.
Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.
Integral linearity error/Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

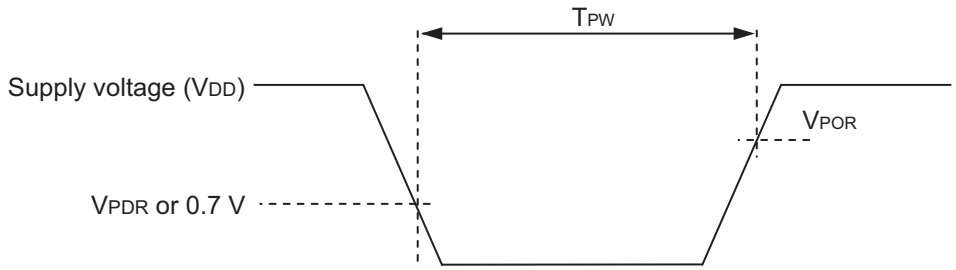
5. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

2.6.3 POR circuit characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.47	1.51	1.55	V
	V_{PDR}	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width[Note]	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3. ELECTRICAL SPECIFICATIONS (G: T_A = -40 to +105°C)

This chapter describes the electrical specifications for the products "G: Industrial applications (T_A = -40 to +105°C)".

Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. With products not provided with an EV_{DD} or EV_{SS} pin, replace EV_{DD} with V_{DD}, or replace EV_{SS} with V_{SS}.

3. For derating with T_A = +85 to +105°C, contact our Sales Division or the vender's sales division. Derating means the specified reduction in an operating parameter to improve reliability.

(4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			**Note 1**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.0 Note 2	Mbps
			2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			**Note 3**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4	Mbps
			2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			**Note 5**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 6	Mbps

Notes 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

2. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

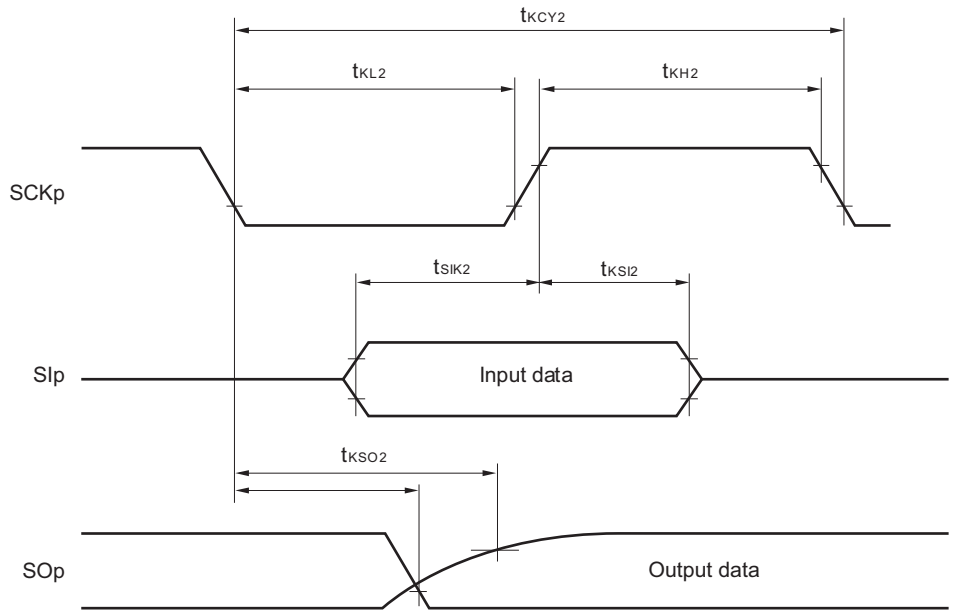
$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

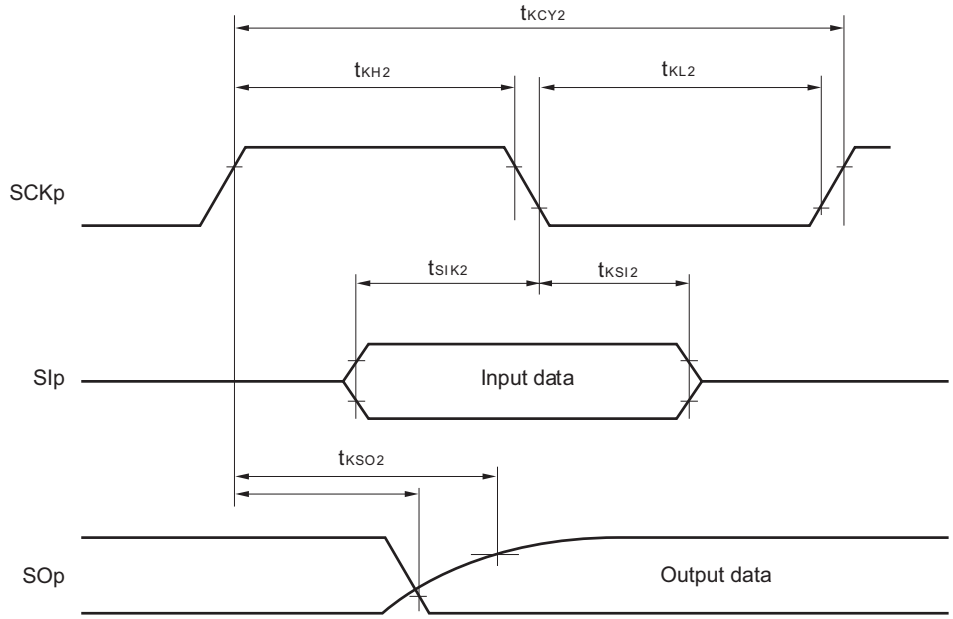
* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01), m: Unit number (m = 0),
n: Channel number (n = 0, 1), g: PIM and POM number (g = 1)

(2) I^2C fast mode

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: f_{CLK} ≥ 3.5 MHz	2.7 V ≤ EV_{DD} ≤ 5.5 V	0	400	kHz
			2.4 V ≤ EV_{DD} ≤ 5.5 V	0	400	
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.6		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0.6		
Hold time Note 1	$t_{HD:STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.6		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0.6		
Hold time when SCLA0 = “L”	t_{LOW}	2.7 V ≤ EV_{DD} ≤ 5.5 V		1.3		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		1.3		
Hold time when SCLA0 = “H”	t_{HIGH}	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.6		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0.6		
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		100		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		100		
Data hold time (transmission) Note 2	$t_{HD:DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0	0.9	μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0	0.9	
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.6		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0.6		
Bus-free time	t_{BUF}	2.7 V ≤ EV_{DD} ≤ 5.5 V		1.3		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		1.3		

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the $\overline{ACK}$ (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0, ANI1	–	Refer to **3.6.1 (3)**.	Refer to **3.6.1 (4)**.
ANI16 to ANI23	Refer to **3.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **3.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	2.4 V ≤ AV_{REFP} ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
Integral linearity error [Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±2.5	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±1.5	LSB
Analog input voltage	V_{AIN}	Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} [Note 4]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} [Note 4]			V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.
Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.
Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0, ANI1, ANI16 to ANI23, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	t_{CONV}	10-bit resolution	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	E_{ZS}	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Full-scale error Notes 1, 2	E_{FS}	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Analog input voltage	V_{AIN}	ANI0, ANI1		0		V_{DD}	V
		ANI16 to ANI23		0		EV_{DD}	V
		Internal reference voltage output (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} Note 3			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} Note 3			V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

3.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V, HS (high-speed main) mode)

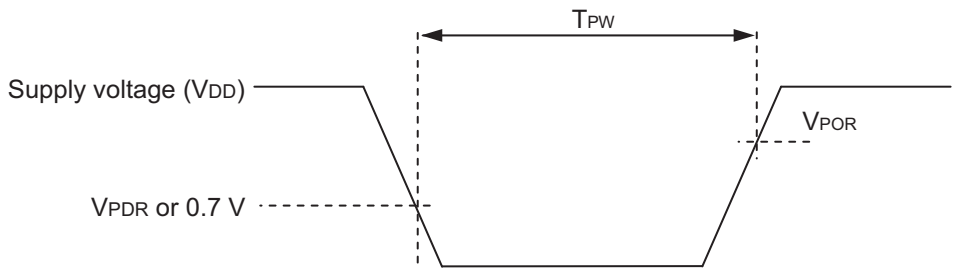
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		–3.6		mV/°C
Operation stabilization wait time	t_{AMP}		5			μs

3.6.3 POR circuit characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.45	1.51	1.57	V
	V_{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width	T_{PW}		300			μs

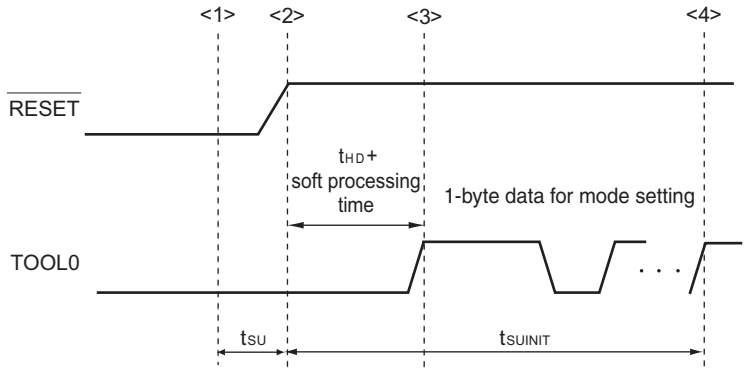
Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.11 Timing Specifications for Switching Flash Memory Programming Modes

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

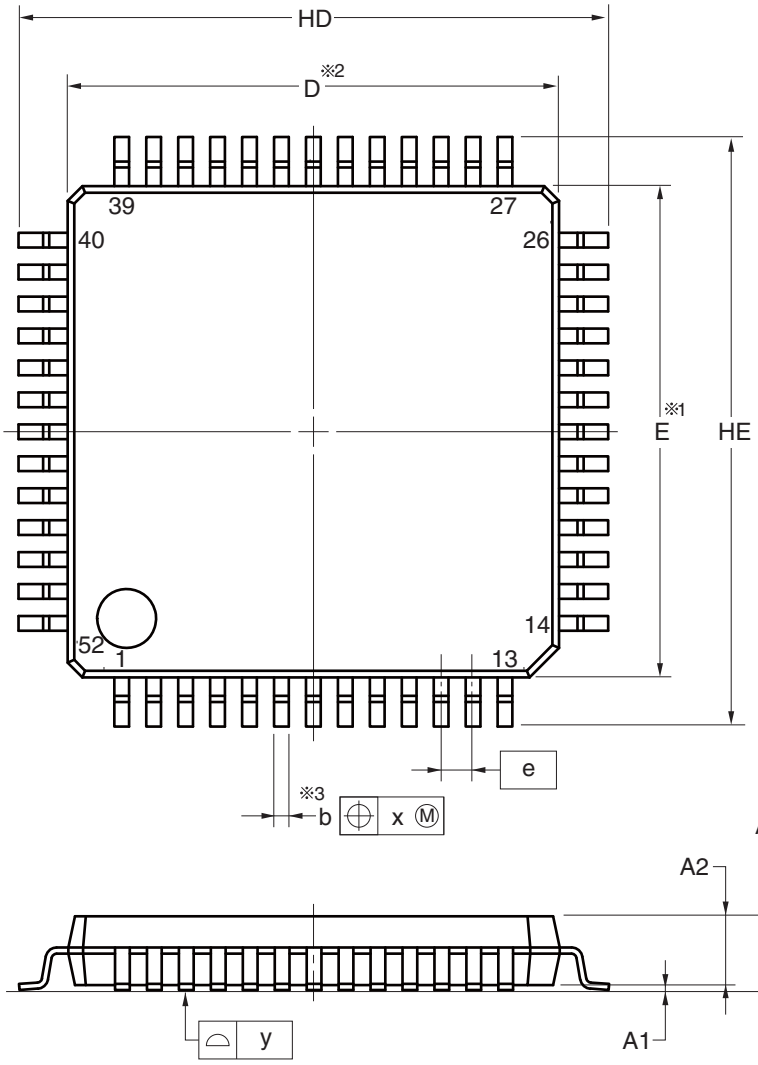
t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

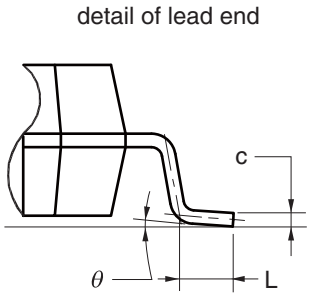
t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

4.4 52-pin Products

R5F10RJ8AFA, R5F10RJAAFA, R5F10RJCAFA
R5F10RJ8GFA, R5F10RJAGFA, R5F10RJCGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3





(UNIT:mm)

ITEM	DIMENSIONS
D	10.00±0.10
E	10.00±0.10
HD	12.00±0.20
HE	12.00±0.20
A	1.70 MAX.
A1	0.10±0.05
A2	1.40
b	0.32±0.05
c	0.145±0.055
L	0.50±0.15
θ	0° to 8°
e	0.65
x	0.13
y	0.10

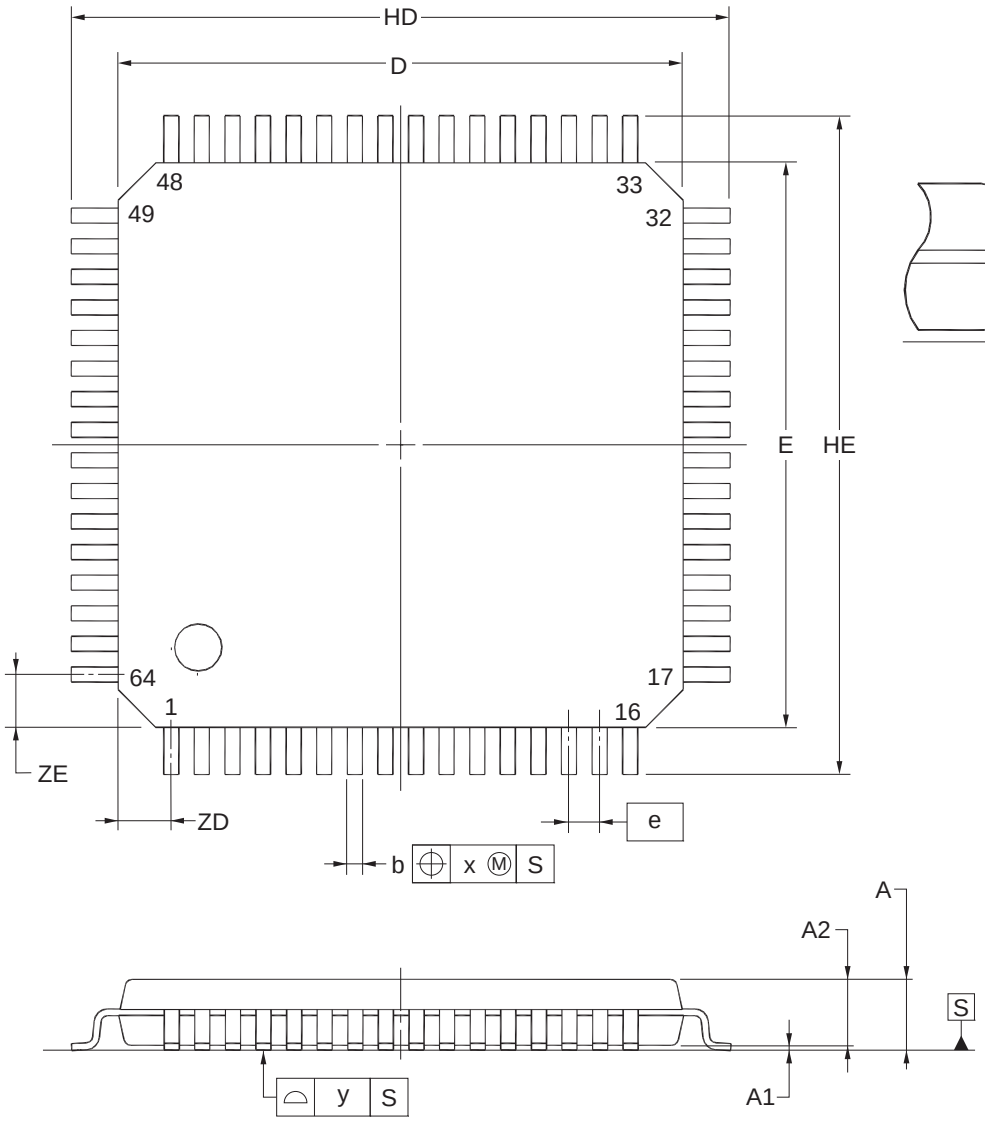
NOTE1.Dimensions "※1" and "※2" do not include mold flash.

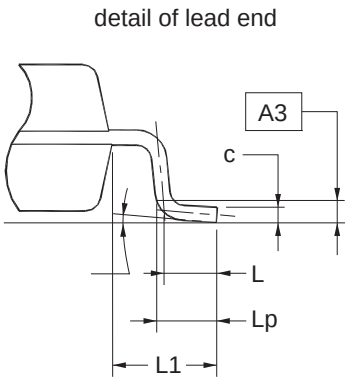
2.Dimension "※3" does not include trim offset.

4.5 64-pin Products

R5F10RLAAFA, R5F10RLCAFA
R5F10RLAGFA, R5F10RLCGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51





(UNIT:mm)

ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	$0.32^{+0.08}_{0.07}$
c	$0.145^{+0.055}_{0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
	$3^{\circ}{}^{+5^{\circ}}_{3^{\circ}}$
e	0.65
x	0.13
y	0.10
ZD	1.125
ZE	1.125

NOTE
Each lead centerline is located within 0.13 mm of its true position at maximum material condition.